

PRODUCT CHARACTERISTICS

VDSS	650V
$R_{DS(on)typ}(V_{GS}=10V)$	4.3Ω
Qg@type	14nC
ID	2A

APPLICATIONS

- * High efficiency switch mode power supplies
- * Electronic lamp ballasts based on half bridge
- * LED power supplies

FEATURES

- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT2N65D	TO-252	2500 pieces /Reel
N/A	MOT2N65C	TO-251	70 pieces/Tube

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

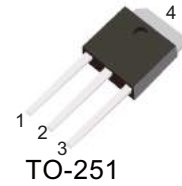
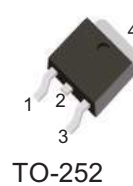
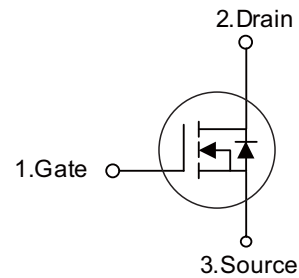
PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V _{DSS}	650	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Avalanche Current (Note 2)	I _{AR}	2.0	A	
Drain Current	Continuous	I _D	2.0	A
	Pulsed (Note 2)	I _{DM}	8.0	A
Avalanche Energy Single Pulsed (Note 3)	E _{AS}	110	mJ	
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns	
Power Dissipation TO-251/TO-252	P _D	44	W	
Junction Temperature	T _J	+150	°C	
Operating Temperature	T _{OPR}	-55 ~ +150	°C	
Storage Temperature	T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J.
3. L=55mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD}≤2.4A, di/dt≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

Symbol

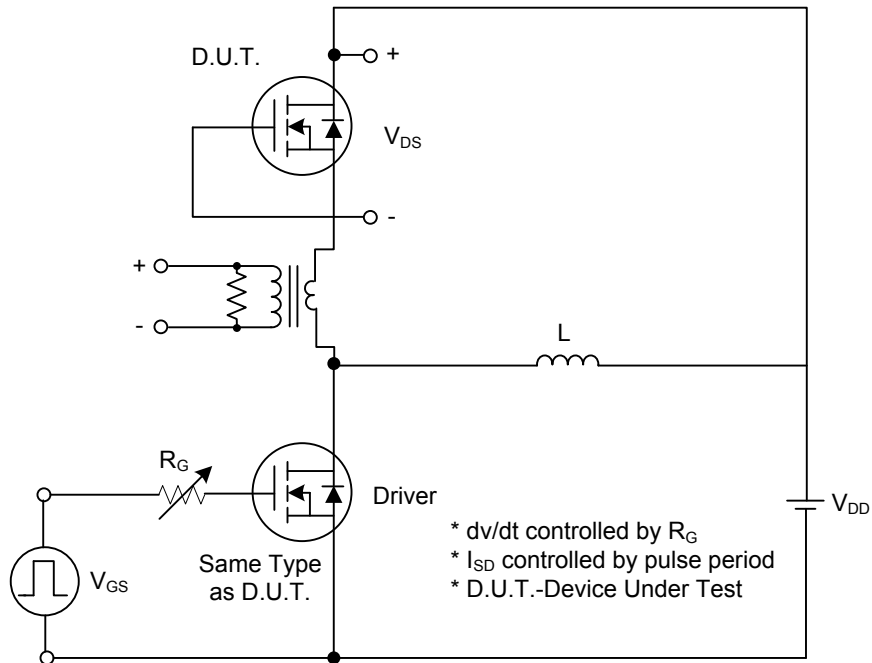


■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

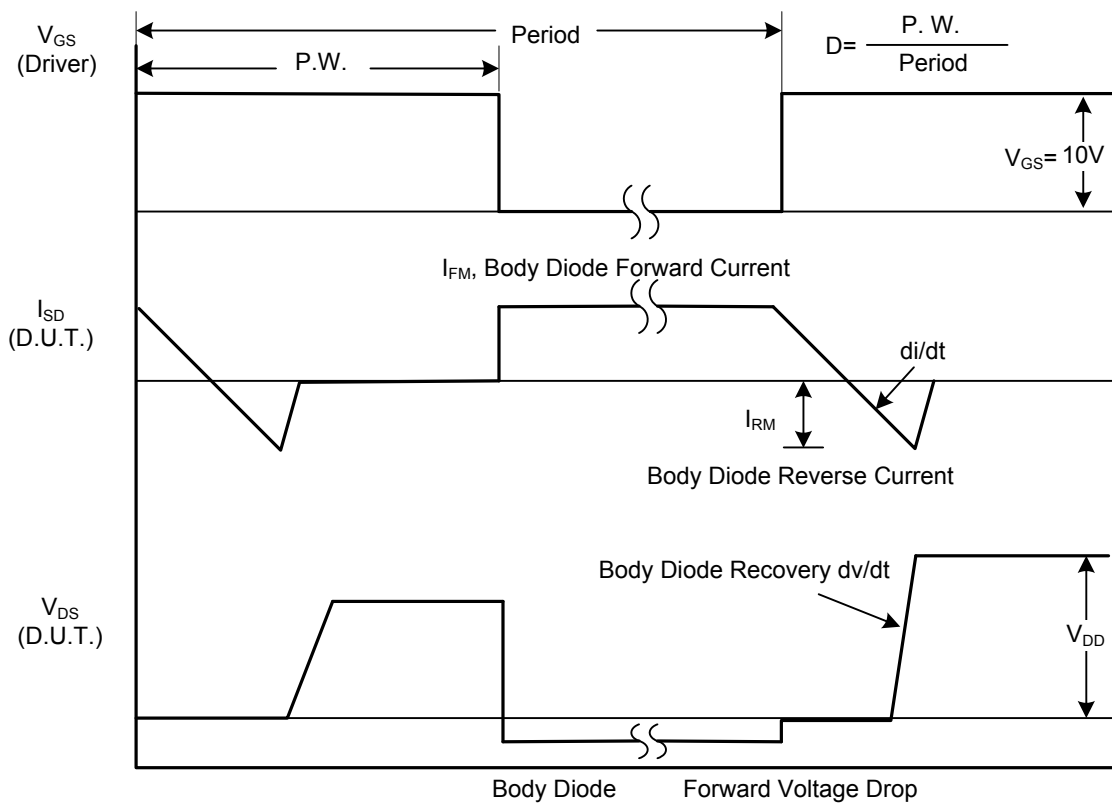
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$	-	-	10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	-	-	100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\mu A$, Referenced to 25°C	-	0.4	-	$V/^\circ\text{C}$
On characteristics						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$	-	4.3	6.0	Ω
Dynamic characteristics						
Input Capacitance	C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1\text{MHz}$	-	240	-	pF
Output Capacitance	C_{OSS}		-	35	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	4.6	-	pF
Switching characteristics						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, I_D = 0.5A,$ $R_G = 25\Omega$ (Note 1, 2)	-	40	-	ns
Turn-On Rise Time	t_R		-	40	-	ns
Turn-Off Delay Time	$t_{D(OFF)}$		-	50	-	ns
Turn-Off Fall Time	t_F		-	22	-	ns
Total Gate Charge	Q_G	$V_{DS} = 50V, V_{GS} = 1.0V,$ $I_D = 1.3A$ (Note 1, 2)	-	12	-	nC
Gate-Source Charge	Q_{GS}		-	5.2	-	nC
Gate-Drain Charge	Q_{GD}		-	2	-	nC
Drain-source diode characteristics						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_{SD} = 2.0A$	-	-	1.4	V
Continuous Drain-Source Current	I_{SD}		-	-	2.0	A
Pulsed Drain-Source Current	I_{SM}		-	-	8.0	A

- Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

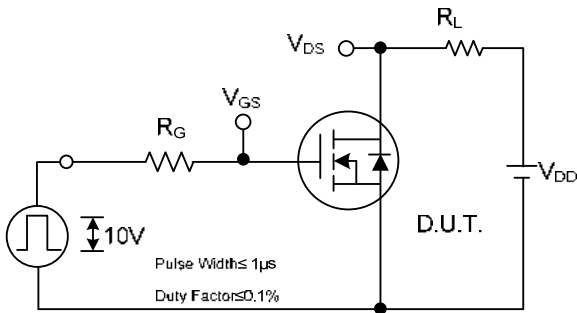


Peak Diode Recovery dv/dt Test Circuit

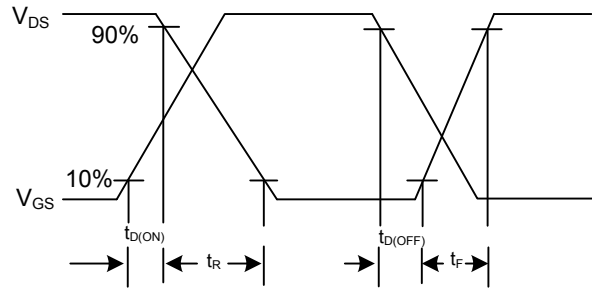


Peak Diode Recovery dv/dt Waveforms

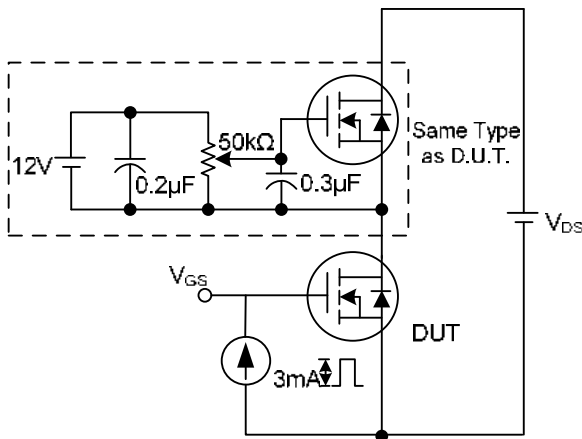
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



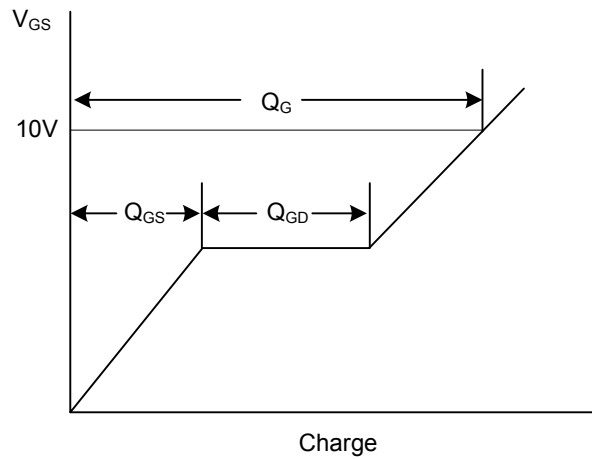
Switching Test Circuit



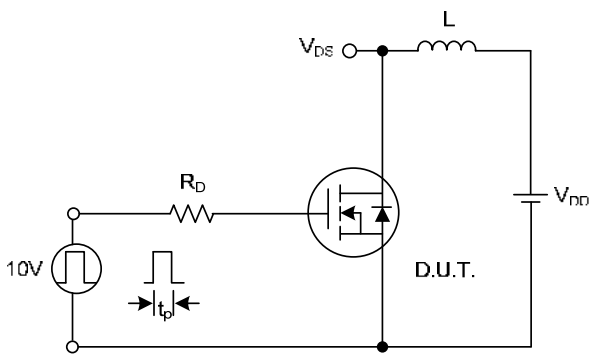
Switching Waveforms



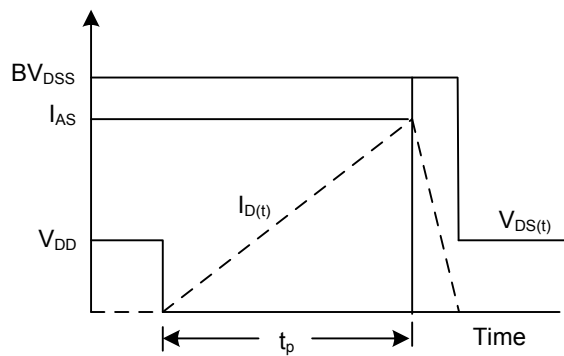
Gate Charge Test Circuit



Gate Charge Waveform

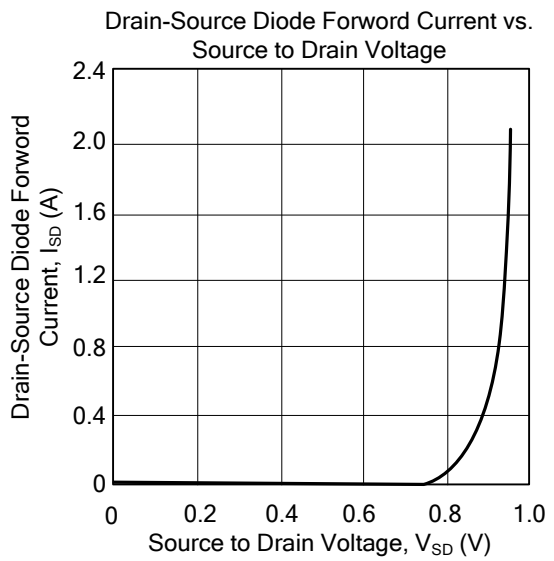
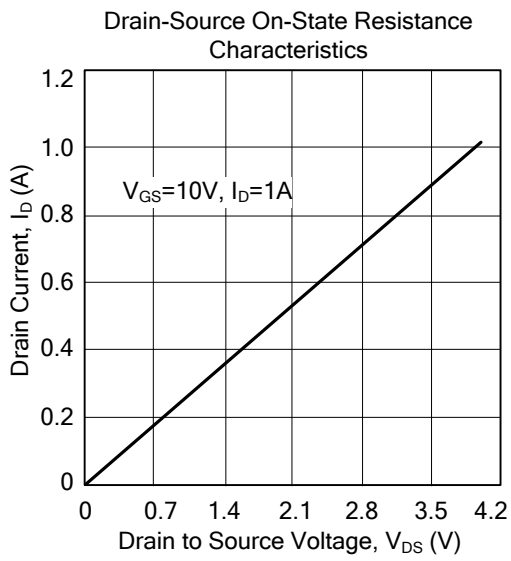
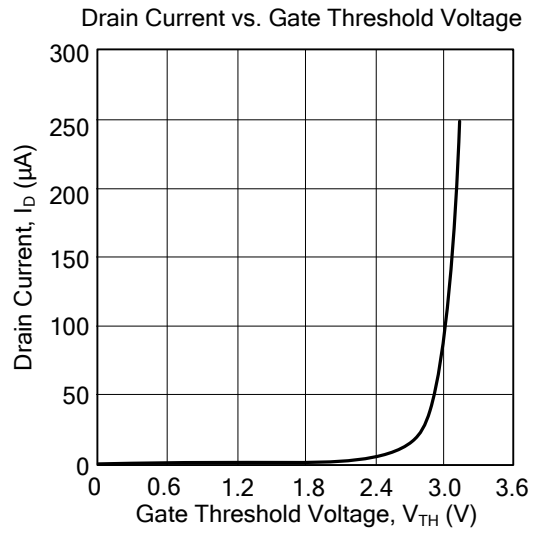
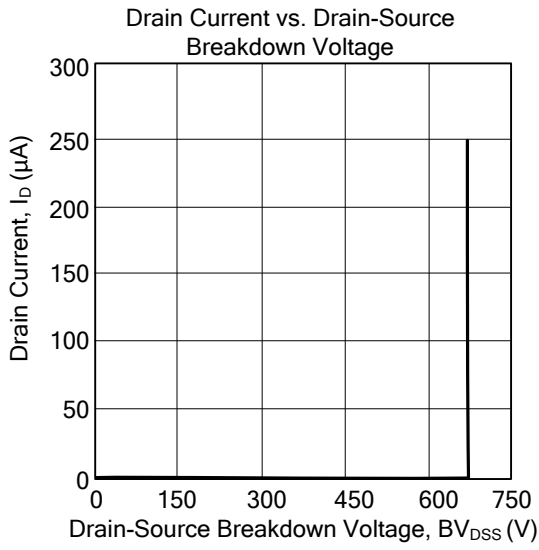


Unclamped Inductive Switching Test Circuit

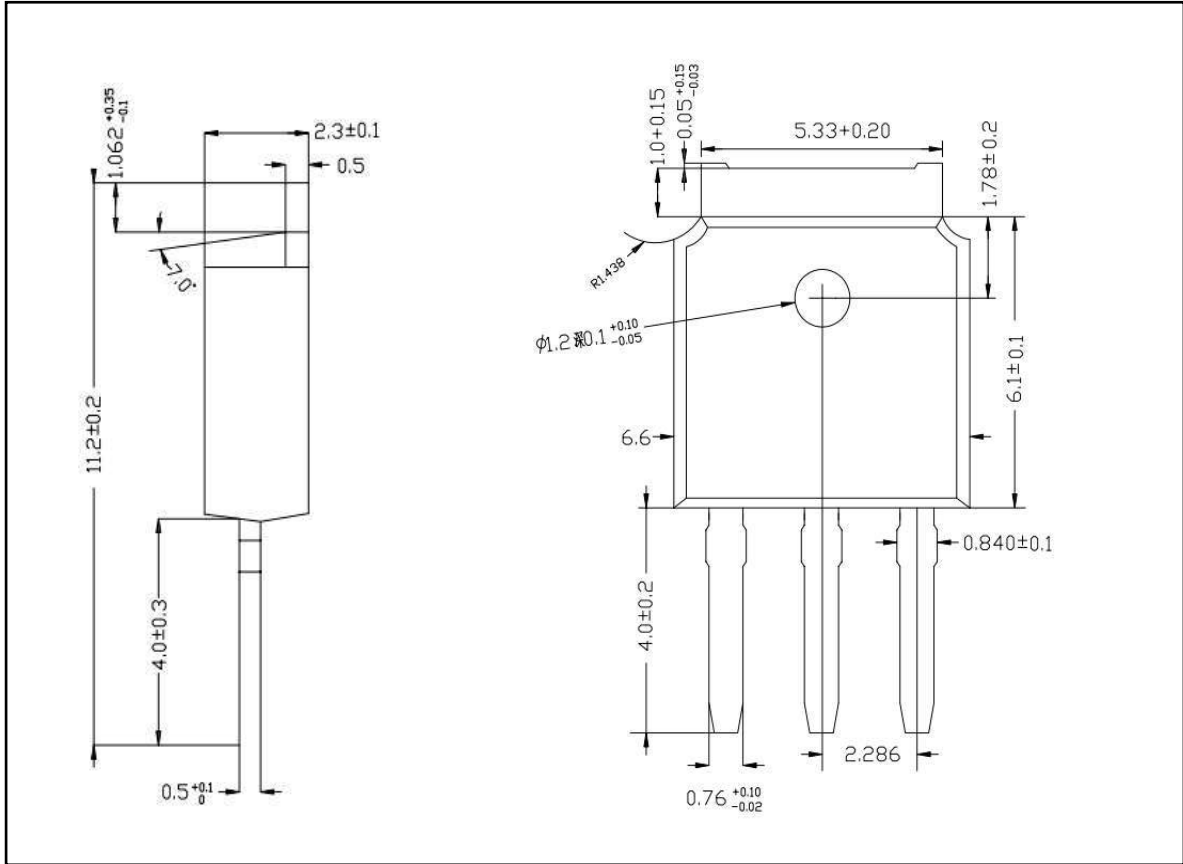


Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TO-251 PACKAGE OUTLINE DIMENSIONS



■ TO-252 PACKAGE OUTLINE DIMENSIONS

